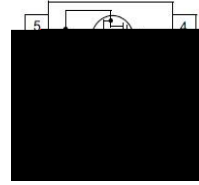


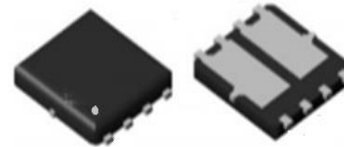
Product Summary

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.



Trench technology
 $R_{DS(ON)}$ to minimize conductive loss

Dual DIE in one package



Power Management in Notebook Computer
 Portable Equipment and Battery Powered
 Systems

Part NO.	ZMD68601N
Marking	ZMD68601
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	23	A
	$I_{D@TC=75}$	17	A
	$I_{D@TC=100}$	14	A
Pulsed Drain Current	I_{DM}	46	A
Total Power Dissipation	$P_D@TC=25$	20	W
Total Power Dissipation	$P_D@TA=25$	1.7	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	90	mJ



Fig.1 Power Dissipation

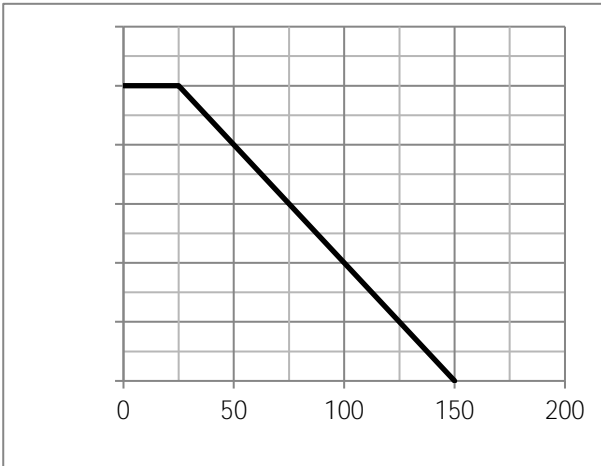


Fig.2 Typical output Characteristics

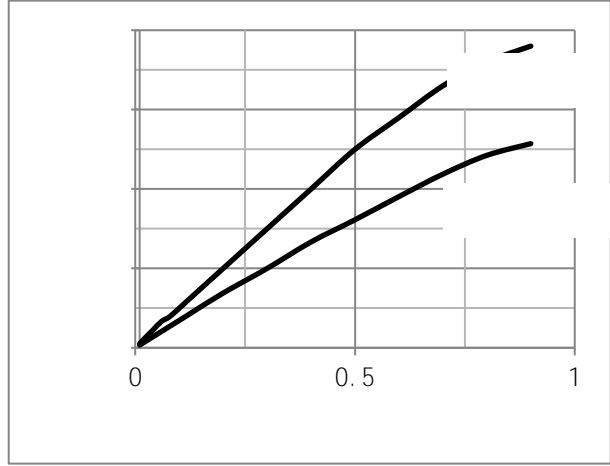


Fig.3 Threshold Voltage V.S Junction Temperature

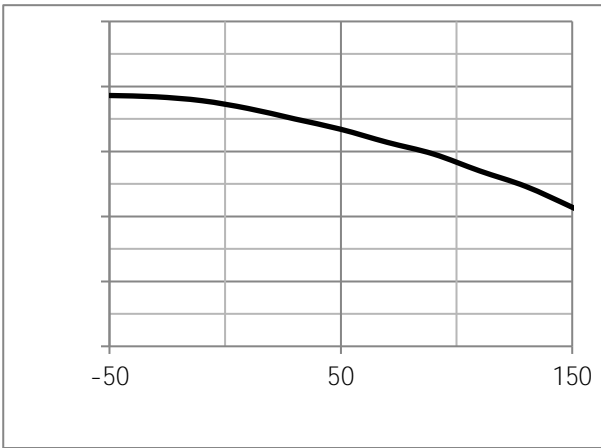


Fig.4 Resistance V.S Drain Current

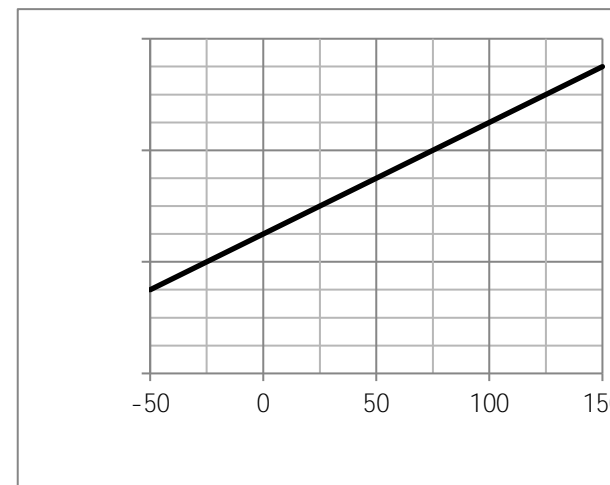
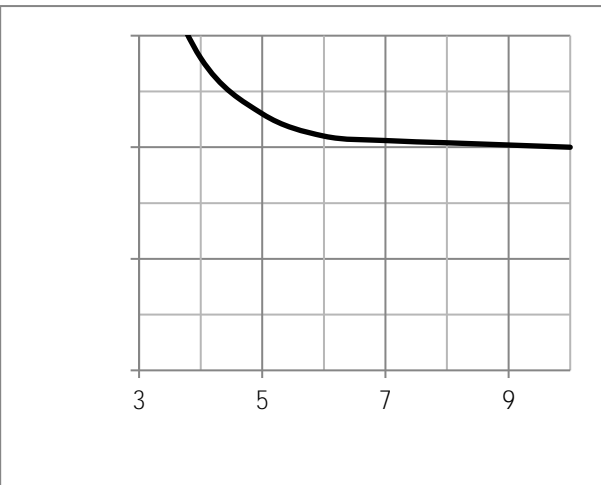
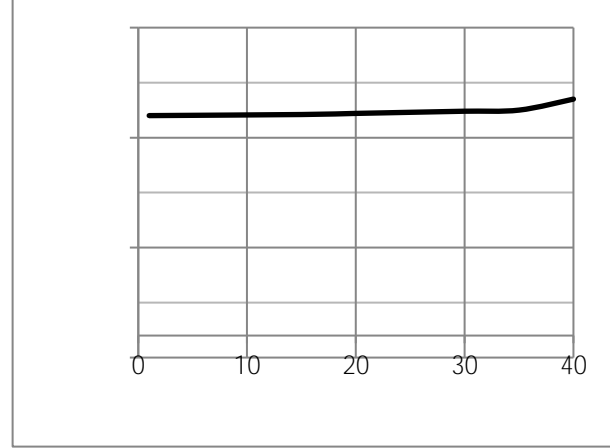




Fig.7 Switching Time Measurement Circuit

Fig.8 Gate Charge Waveform

Fig.9 Switching Time Measurement Circuit

Fig.10 Gate Charge Waveform

Fig.11 Avalanche Measurement Circuit

Fig.12 Avalanche Waveform

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